

Fast Turn-off Thyristor Stud Types P0431SX04# to P0431SX06#

The data sheet on the subsequent pages of this document is a scanned copy of existing data for this product.

(Rating Report 85TR7 Issue 1)

This data reflects the old part number for this product which is: P270PH02-05.
This part number must **NOT** be used for ordering purposes – please use the ordering particulars detailed below.

The limitations of this data are as follows:
Only SC outline drawing (W18) in datasheet
Device no longer available for grade 02 (200V V_{RRM}/V_{DRM})

The following links will direct you to the appropriate outline drawings

[Outline W18](#) – ¾" Ceramic stud
[Outline W25](#) – ¾" Ceramic stud removed

Where any information on the product matrix page differs from that in the following data, the product matrix must be considered correct

An electronic data sheet for this product is presently in preparation.

For further information on this product, please contact your local ASM or distributor.

Alternatively, please contact Westcode as detailed below.

Ordering Particulars			
P0431	SX	◆◆	0
Fixed Type Code	SC – ¾" Ceramic stud SD – ¾" Ceramic stud removed	Voltage code $V_{RRM}/100$ 04-06	Fixed turn-off time code B = 12µs, C = 15µs
Typical Order Code: P0431SD06C, ¾" Ceramic stud removed, 600V V_{RRM}/V_{DRM} , 15µs tq			

IXYS Semiconductor GmbH
Edisonstraße 15
D-68623 Lampertheim
Tel: +49 6206 503-0
Fax: +49 6206 503-627
E-mail: marcom@ixys.de

WESTCODE
An  IXYS Company

IXYS Corporation
3540 Bassett Street
Santa Clara CA 95054 USA
Tel: +1 (408) 982 0700
Fax: +1 (408) 496 0670
E-mail: sales@ixys.net

www.westcode.com

www.ixys.com

Westcode Semiconductors Ltd
Langley Park Way, Langley Park,
Chippenham, Wiltshire, SN15 1GE.
Tel: +44 (0)1249 444524
Fax: +44 (0)1249 659448
E-mail: WSL.sales@westcode.com

Westcode Semiconductors Inc
3270 Cherry Avenue
Long Beach CA 90807 USA
Tel: +1 (562) 595 6971
Fax: +1 (562) 595 8182
E-mail: WSI.sales@westcode.com

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In the interest of product improvement, Westcode reserves the right to change specifications at any time without prior notice.

Devices with a suffix code (2-letter, 3-letter or letter/digit/letter combination) added to their generic code are not necessarily subject to the conditions and limits contained in this report.

QUALITY EVALUATION LABORATORY

Rating Report: 85TR7

Date : 11th July, 1985

Origin:

Pages : 24

Thyristor Type P270PH02-H05

Written: M.F.W. Dunlop

Checked: *mfw*

Approved: *Bleth*

The P270P thyristor series are diffused regenerative gate devices employing a 24 mm slice in a stud based top hat housing.

Ratings and Characteristics

Ratings

Voltage Grades

: H02-H05

V_{DSM}

: 200-500V

V_{RSM}

: 300-600V

V_{DRM}, V_{RRM}

: 200-500V

I_T (AV) : Single phase : 50 Hz, 180° sinewave

$T_{CASE} = 85^{\circ}C$

(See Notes on page 2)

: 226A

I_T (rms) max.

: 355A

I_T d.c. max.

: 355A

I_{TSM} : $t = 10ms$ half sinewave; T_J (initial) = $125^{\circ}C$; $V_{RM} = 0.6V_{RRM}$ (MAX) : 6500A

I_{TSM} : $t = 10ms$ half sinewave; T_J (initial) = $125^{\circ}C$; $V_{RM} \leq 10V$: 7150A

I^2t : $t = 10ms$; T_J (initial) = $125^{\circ}C$; $V_{RM} = 0.6V_{RRM}$ (MAX) : $211 \times 10^3 A^2s$

I^2t : $t = 10ms$; T_J (initial) = $125^{\circ}C$; $V_{RM} \leq 10V$: $256 \times 10^3 A^2s$

I^2t : $t = 3ms$; T_J (initial) = $125^{\circ}C$; $V_{RM} \leq 10V$: $187 \times 10^3 A^2s$

di/dt : (Repetitive) $T_J = 125^{\circ}C$ Gate: 20V, 20 μs Rise time $1\mu s$: 500A/ μs

I_{FGM} : Anode positive with respect to cathode

: 18A

V_{FGM} : " " " " " "

: 12V

V_{RGM} :

: 5V

P_G (AV) :

: 1.5W

P_{GM} :

: 60W

V_{GD} :

: 0.25V

T_C operating range

: -40 to $125^{\circ}C$

T_{stg} Non-operating

: -40 to $150^{\circ}C$

Characteristics

(maximum values unless stated otherwise)

$I_{GT} : T_J = 25^{\circ}\text{C}$	)				: 200mA
$I_H : T_J = 25^{\circ}\text{C}$	)	$V_A = 6\text{V}$	$I_A = 1\text{A}$		: 600mA
$V_{GT} : T_J = 25^{\circ}\text{C}$	)				: 3V
$V_O : T_J = 125^{\circ}\text{C}$					: 0.95V
$r_T : T_J = 125^{\circ}\text{C}$					: 0.377mohms
$V_{TM} : I_{TM} = 600\text{A}$		$T_{VJ} = 125^{\circ}\text{C}$			: 1.18V
$R_{th} (\text{J/C})$					: 0.12 $^{\circ}\text{C/W}$
dV/dt : Linear ramp to 0.8V _{DRM} (max). $T_J = 125^{\circ}\text{C}$; Gate O/C; repetitive : 200V/ μS *					
$I_{DRM} : T_J = 125^{\circ}\text{C}$	$V_{DM} = V_{DRM}(\text{max})$				: 30 mA
$I_{RRM} : T_J = 125^{\circ}\text{C}$	$V_{RM} = V_{RRM}(\text{max})$				: 30mA
$Q_{RR} : I_{TM} = 300\text{A}$	$dI/dt = 20 \text{ A}/\mu\text{S}$, 50% chord value				
	$V_{RM} : 50\text{V}$	$T_{VJ} = 125^{\circ}\text{C}$			: 106 μC typ.
$t_q : I_{TM} = 300\text{A}$	$dI/dt = 20 \text{ A}/\mu\text{S}$; $T_J = 125^{\circ}\text{C}$	$V_{RM} = 50\text{V}$			
	$dV/dt = 200\text{V}/\mu\text{S}$ to 0.8V _{DRM}				: 10-25 μS
	When specified, 20V/ μS to 0.8V _{DRM}	Typical			: 8-20 μS
Outline drawing					: 101A225
$R_{th} (\text{C-H.S.})$					: 0.04 $^{\circ}\text{C/W}$
Mounting torque					: 2.5-2.77Kg.f-m
Outline (JEDEC NO.)					:

Extension of Turn-off Time

This report is applicable to other t_q /reapplied dV/dt combinations when supply has been agreed by Sales/Production.

*Repetitive dV/dt

Higher dV/dt selections are available up to 1000V/ μS on request.

I_{TAV} at $T_c = 85^{\circ}\text{C}$ limited by s.m.s. current limit

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Voltage Ratings

Voltage Grade	V_{DSM} V_{DRM} V_{RRM} V	V_{RSM} V	V_D V_R DC
02	200	300	140
04	400	500	280
05	500	600	350

Extension of Voltage Grades

This report is applicable to other and higher voltage grades when supply has been agreed by Sales/Production.

2. INTRODUCTION

The P270P thyristor series are diffused regenerative gate devices employing a 24 mm slice in a stud base top hat housing.

3. NOTES ON THE RATINGS

a) Rate of rise of on-state current

The maximum un-primed rate of rise of on-state current must not exceed 1000A/uS at any time during turn-on on a non-repetitive basis. For repetitive performance the on-state rate of rise of current must not exceed 500A/uS at any time during turn-on. Note that these values of current rate of rise apply to the circuit external to the device and its specified snubber network and device current rates of rise will be higher.

b) Square wave ratings

These ratings are given for leading edge linear rates of rise of forward current of 100 and 500 A/uS.

c) Duty Cycle Lines

The 100% duty cycle line appears on all these ratings. These frequency ratings are presented in the form that all duty cycles may be represented by straight parallel lines.

d) Maximum operating frequency

The maximum operating frequency is set by the time required for the thyristor to turn off (t_q) and for the off-state voltage to reach full value (t_v), i.e.

$$f_{\text{max.}} = \frac{1}{t_{\text{pulse}} + t_q + t_v}$$

e) Energy per pulse characteristics

These curves enable rapid estimation of device dissipation to be obtained for conditions not covered by the frequency ratings.

Let E_p be the Energy per pulse for a given current and pulse width, in joules

Let R_{th} be the steady-state thermal resistance (junction to case) and T_{CASE} be the case temperature

Then the average dissipation will be

$$W_{AV} = E_p \times f$$

and

$$T_{CASE} = 125 - W_{AV} R_{th}$$

4. REVERSE RECOVERY LOSS

On account of the number of circuit variables affecting reverse recovery voltage, no allowance for reverse recovery loss has been made in these ratings. The following procedure is recommended for use where it is necessary to include reverse recovery loss.

a) Determination by Measurement

From waveforms of recovery current obtained from a high frequency shunt (see Note 1) and reverse voltage present during recovery, an instantaneous reverse recovery loss waveform must be constructed. Let the area under this waveform be A joules per pulse. A new case temperature can then be evaluated from:

$$T_{\text{CASE (new)}} = T_{\text{CASE (original)}} - A \left(\frac{r_t \cdot 10^6}{t} + R_{th} \times f \right)$$

$$\text{where } r_t = 1.64 \times 10^{-4} \sqrt{t}$$

t = duration of reverse recovery loss per pulse in microseconds

A = Area under reverse loss waveform per pulse in joules (I.W.S.)

f = rated frequency at the original case temperature

The total dissipation is now given by

$$W_{\text{(TOT)}} = W_{\text{(original)}} + A \times f$$

b) Determination without Measurement

In circumstances where it is not possible to measure voltage and current conditions, or for design purposes, the additional losses may be estimated from curves on page 14. A typical R-C snubber network is connected across the thyristor to control the transient reverse voltage waveform.

Let E be the value of energy per reverse cycle in joules (curves on p. 14)

Let f be the operating frequency in Hz

$$\text{then } T_{\text{CASE new}} = T_{\text{CASE original}} - (E \times R_{th} \times f)$$

where $T_{\text{CASE new}}$ is the required maximum case temperature and $T_{\text{CASE original}}$ is the case temperature given with the frequency ratings.

5. GATE DRIVE

The recommended gate drive is 20V, 20ohms with a short-circuit current rise time of not more than 1uS. This gate drive must be applied when using the full di/dt capability of the device.

6. THE DV/DT SUPPRESSION NETWORK

The effect of a conventional resistor-capacitor snubber of 0.22uf 5 ohms has been included in these ratings and all rating di/dt values apply to the circuit external to the thyristor and its suppression network.

7. NOTE 1

REVERSE RECOVERY LOSS BY MEASUREMENT

This thyristor has a low reverse recovered charge and peak reverse recovery current. When measuring the charge care must be taken to ensure that:

- a) a.c. coupled devices such as current transformers are not affected by prior passage of high amplitude forward current.
- b) The measuring oscilloscope has adequate dynamic range - typically 100 screen heights - to cope with the initial forward current without overload.

NOTE 2

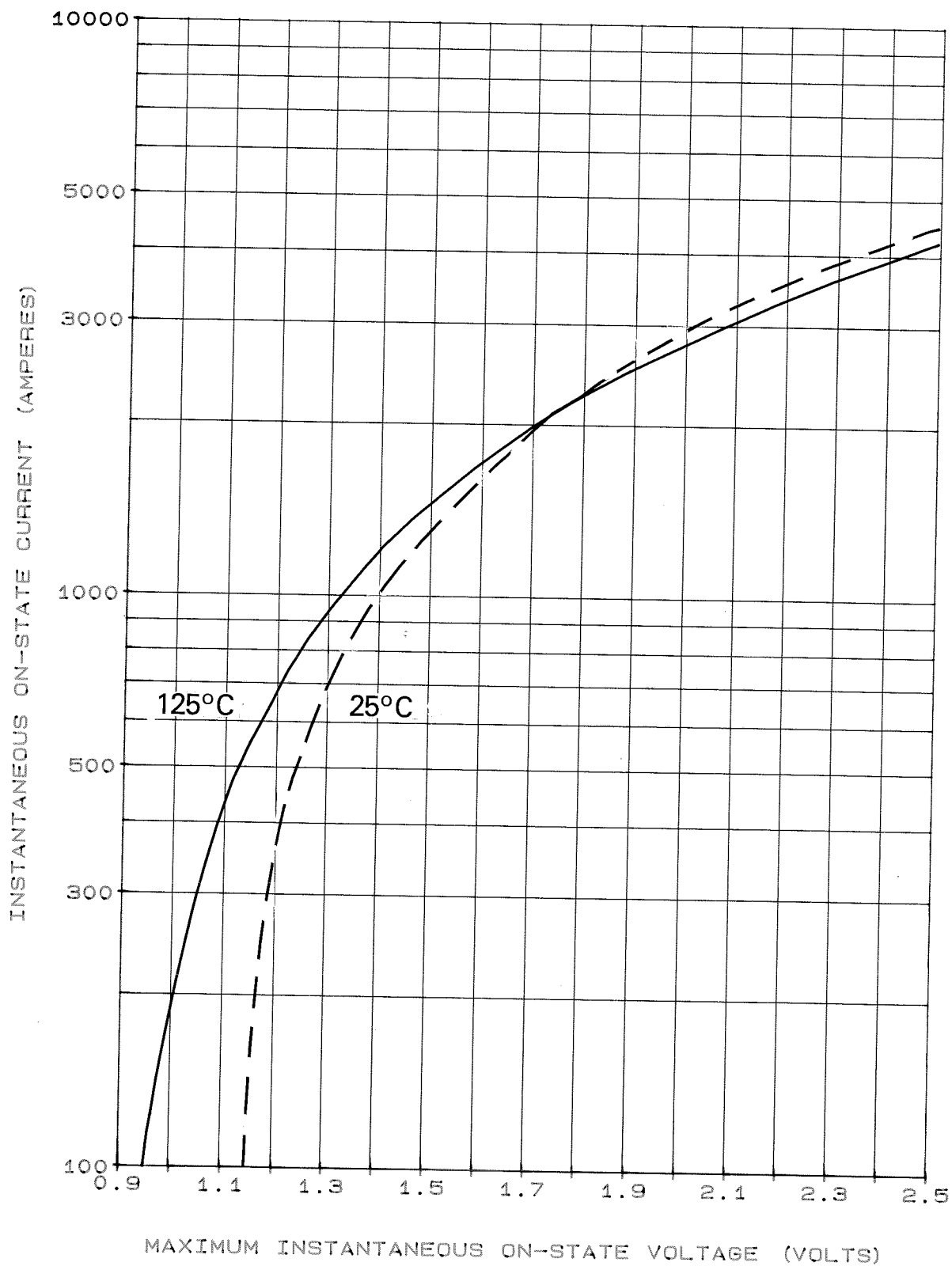
HOUSING LOSS

The loss caused by coupling between housing and anode current (which gives rise to additional heating at high frequency) has been incorporated into the curves of forward energy loss per pulse.

P2701 Fig 16

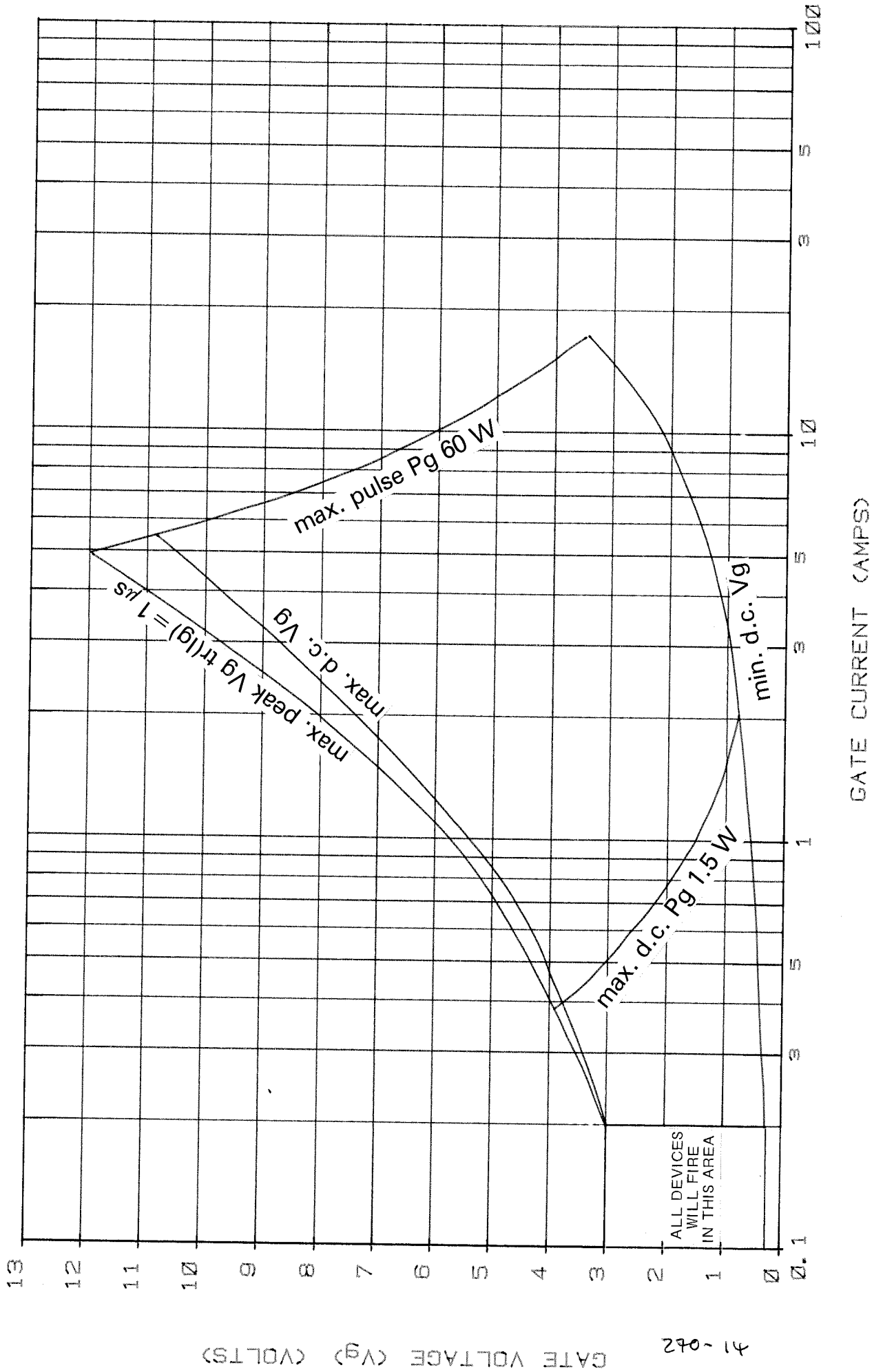
- 8 -

ON-STATE CHARACTERISTIC OF LIMIT DEVICE



270-16

GATE CHARACTERISTICS AT 25°C JUNCTION TEMPERATURE



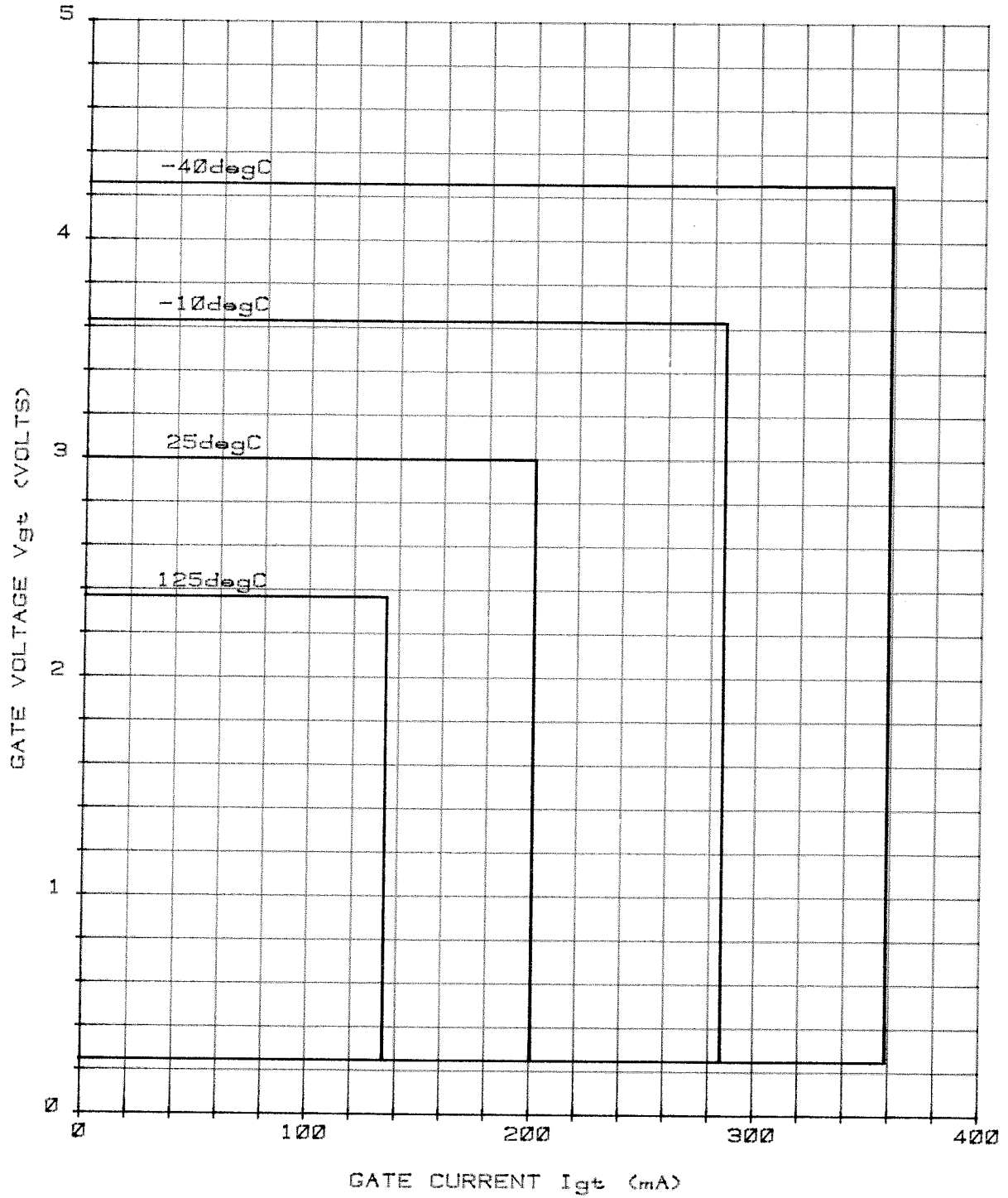
GATE VOLTAGE (V_g) (VOLTS)

41-042

Page 10

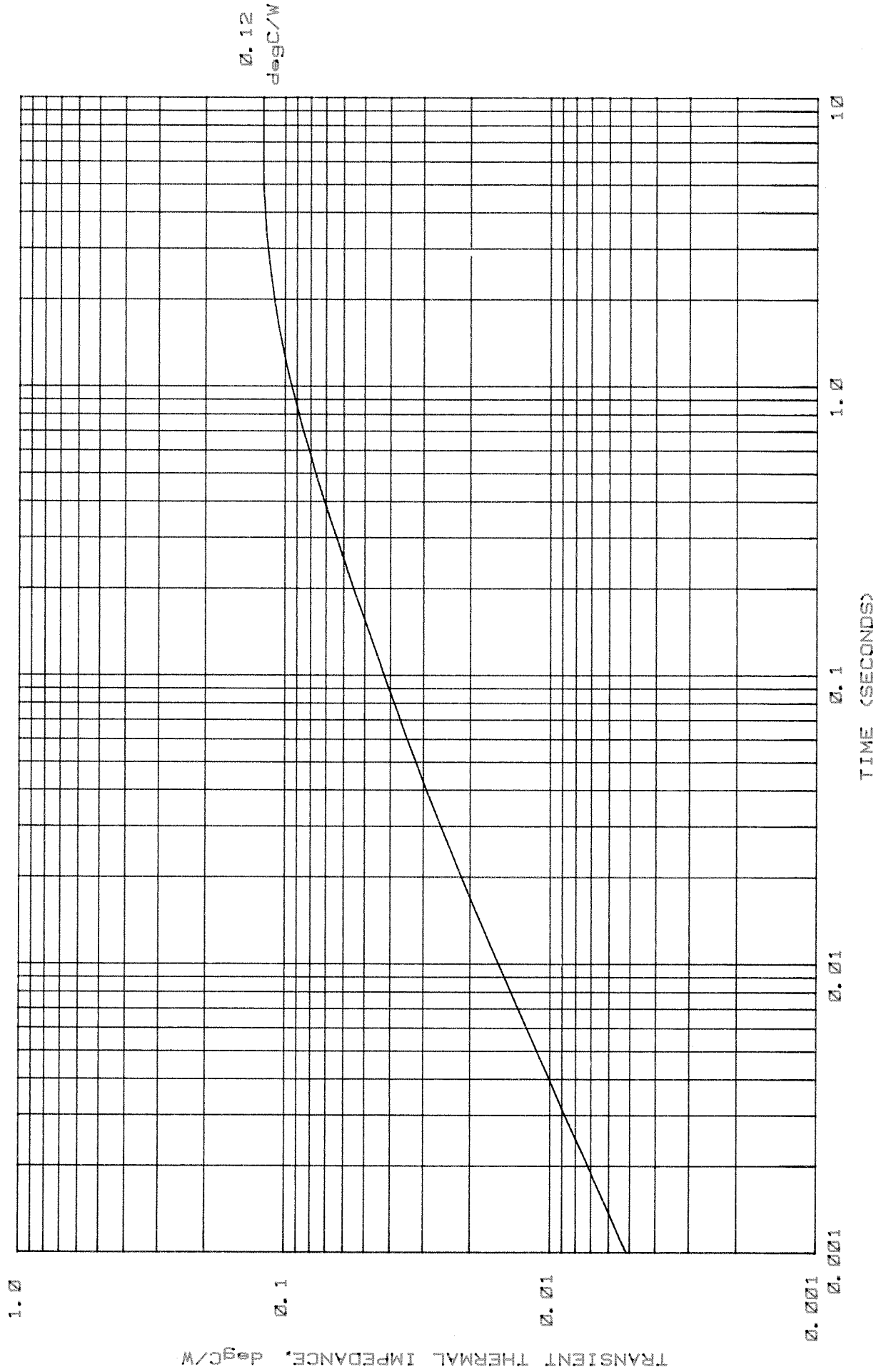
GATE TRIGGERING CHARACTERISTICS

(TRIGGER POINTS OF ALL THYRISTORS LIE IN THE AREAS SHOWN)



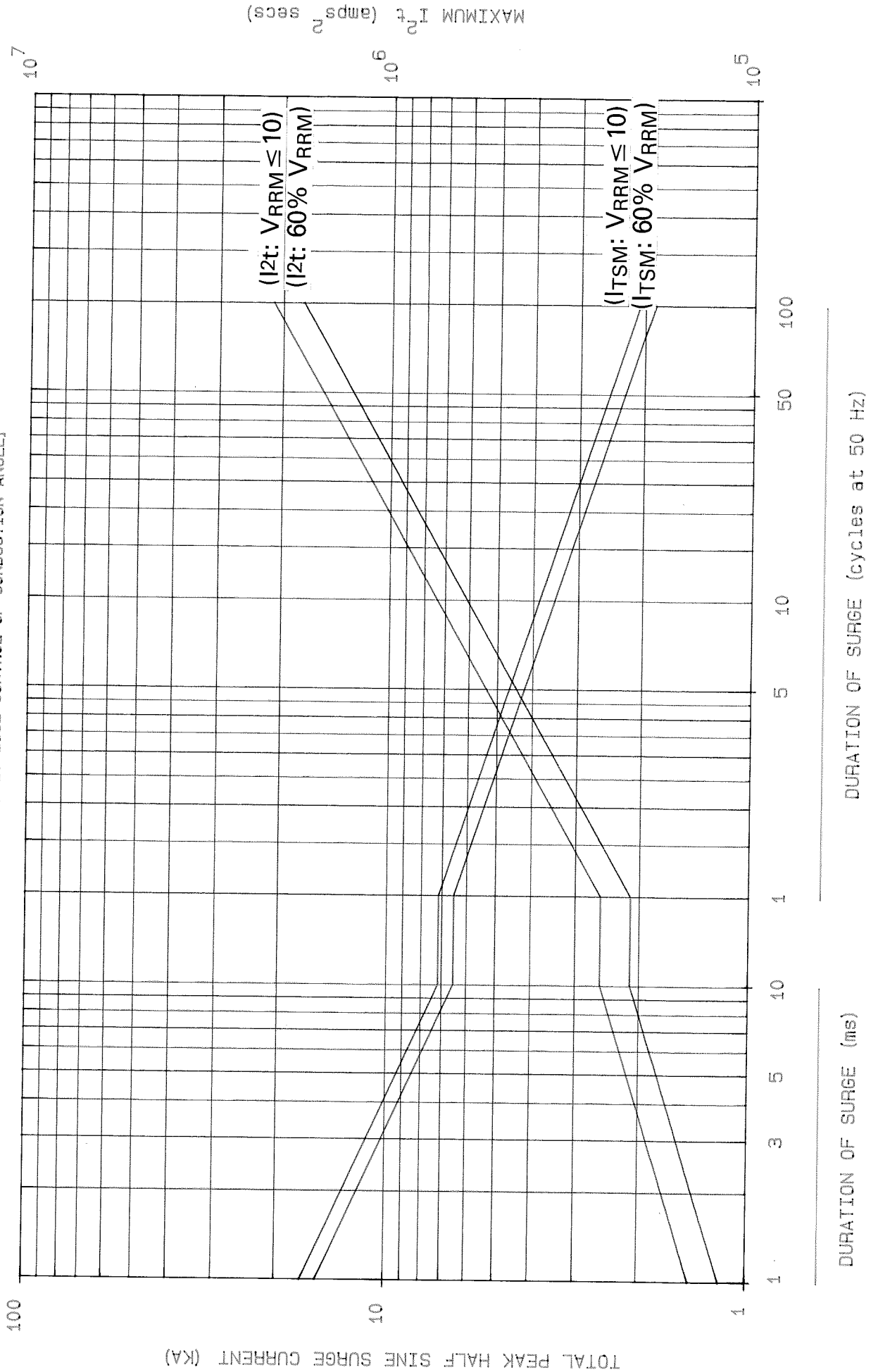
P270P Fig 12

JUNCTION TO CASE TRANSIENT THERMAL IMPEDANCE



P9102 Fig. 13

MAXIMUM NON REPETITIVE SURGE CURRENT AT INITIAL JUNCTION TEMPERATURE 125°C
[GATE MAY TEMPORARILY LOSE CONTROL OF CONDUCTION ANGLE]

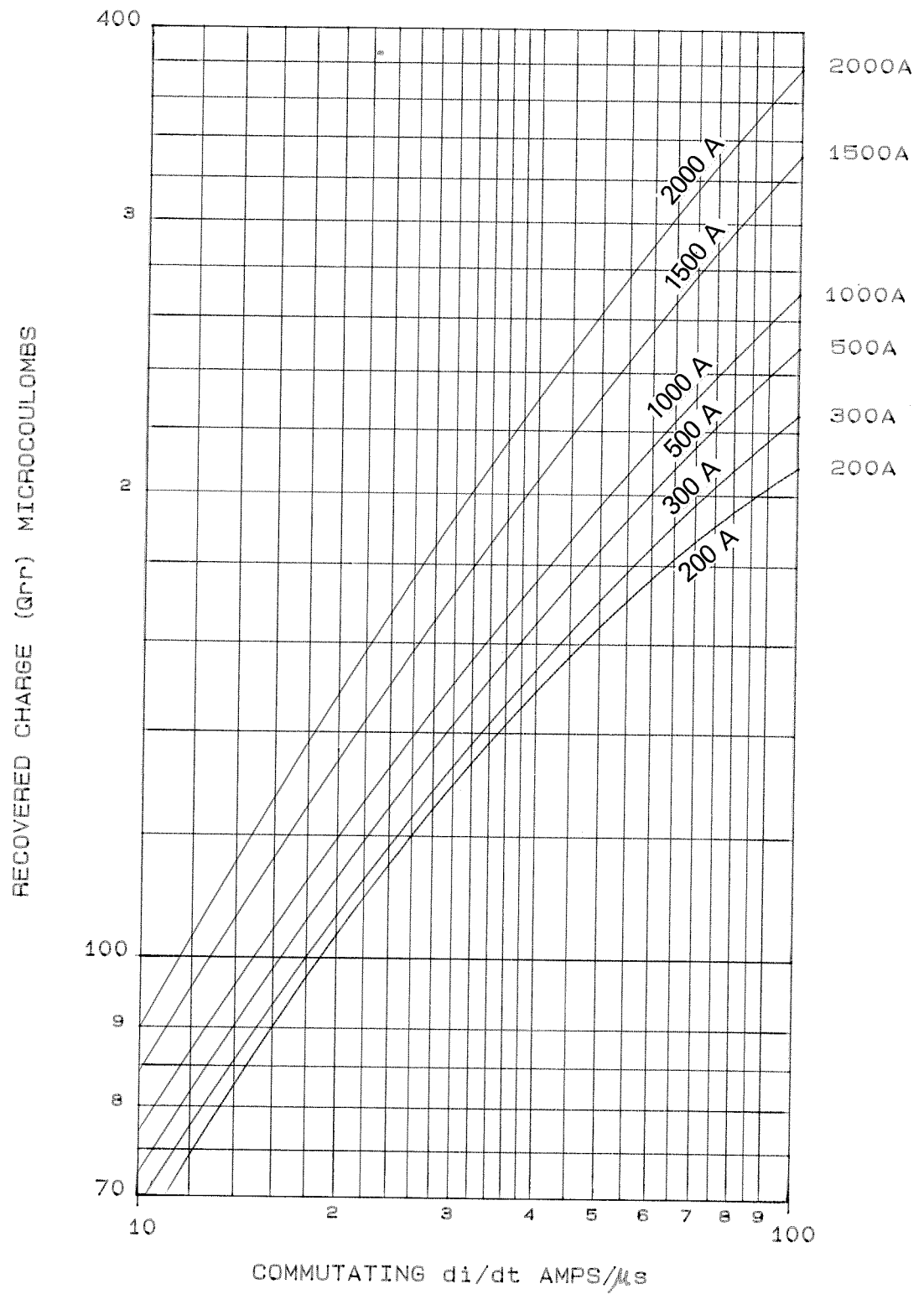


TOTAL PEAK HALF SINE SURGE CURRENT (KA)

21-072

422 1002 1.8 11

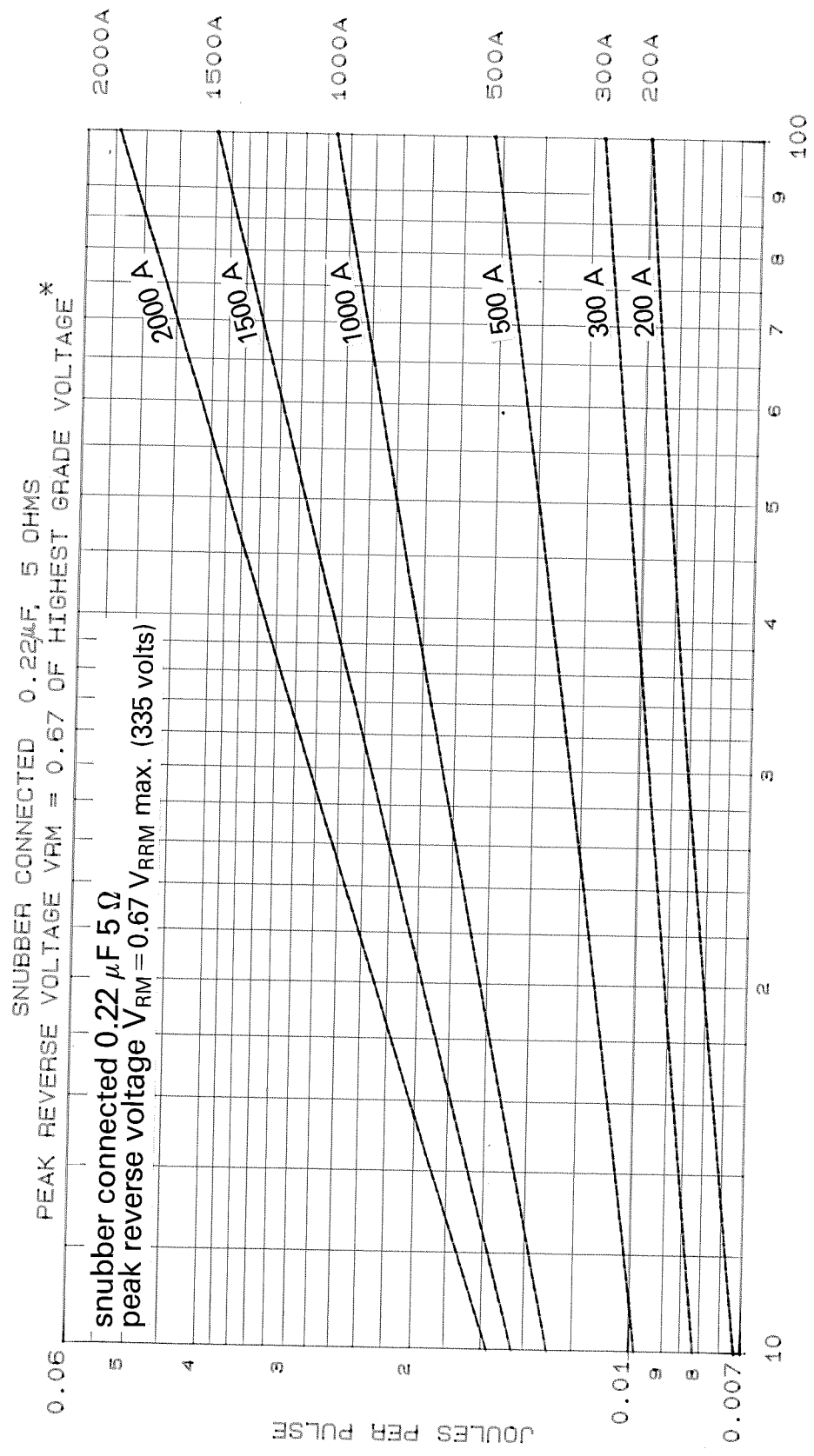
TYPICAL RECOVERED CHARGE AT 125°C JUNCTION TEMPERATURE



270-11

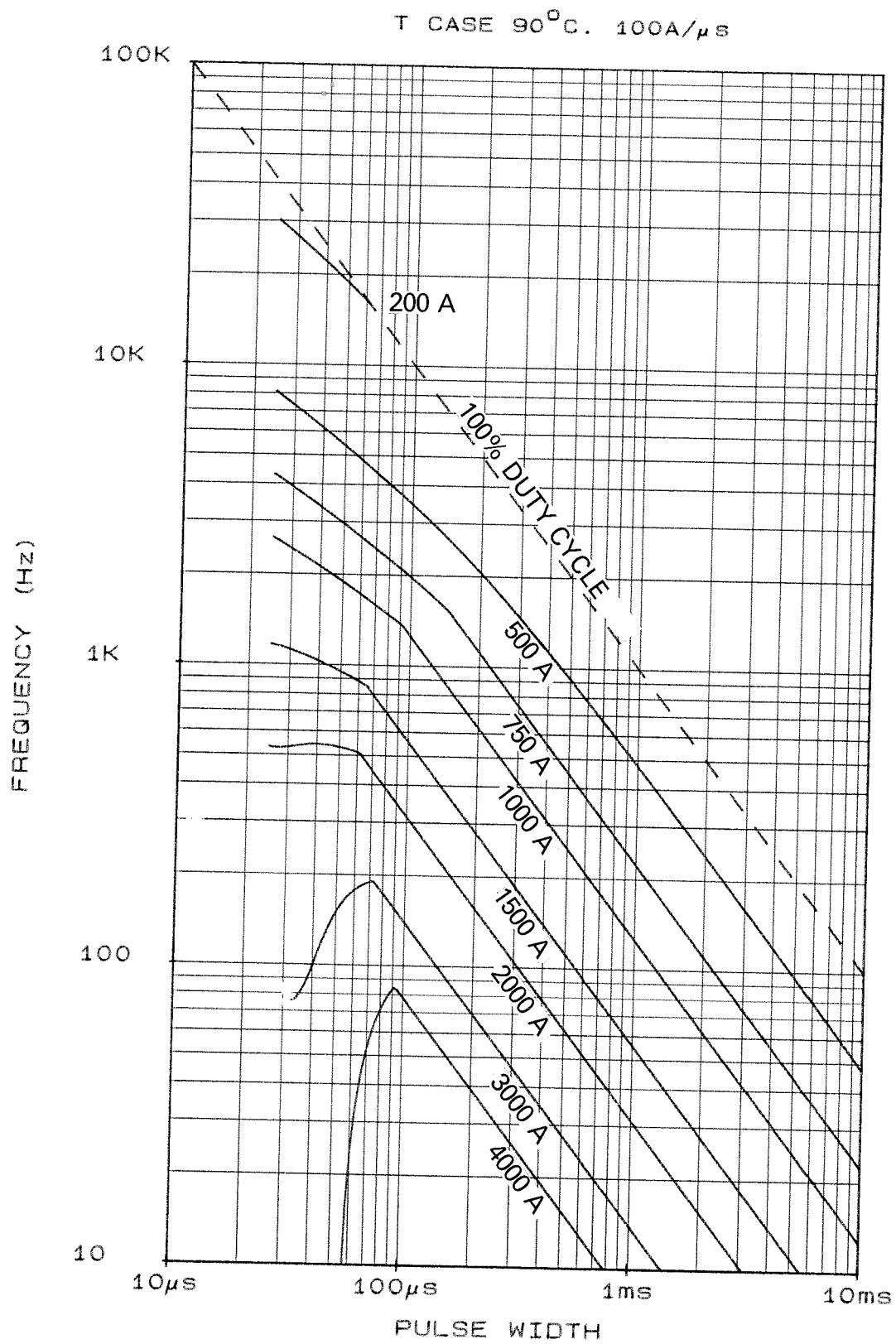
927102-1

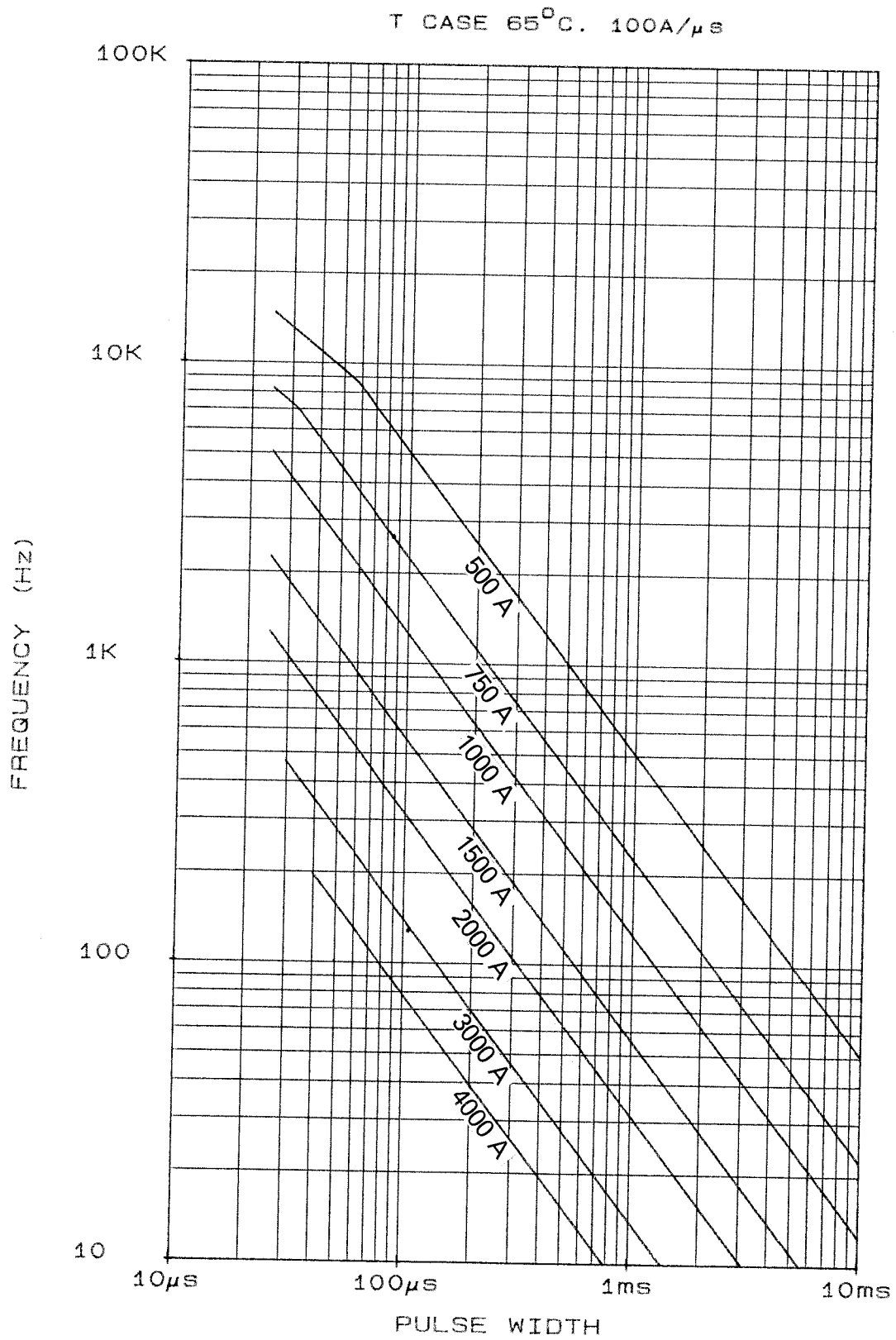
MAXIMUM REVERSE RECOVERY ENERGY LOSS PER PULSE, 125°C JUNCTION TEMPERATURE



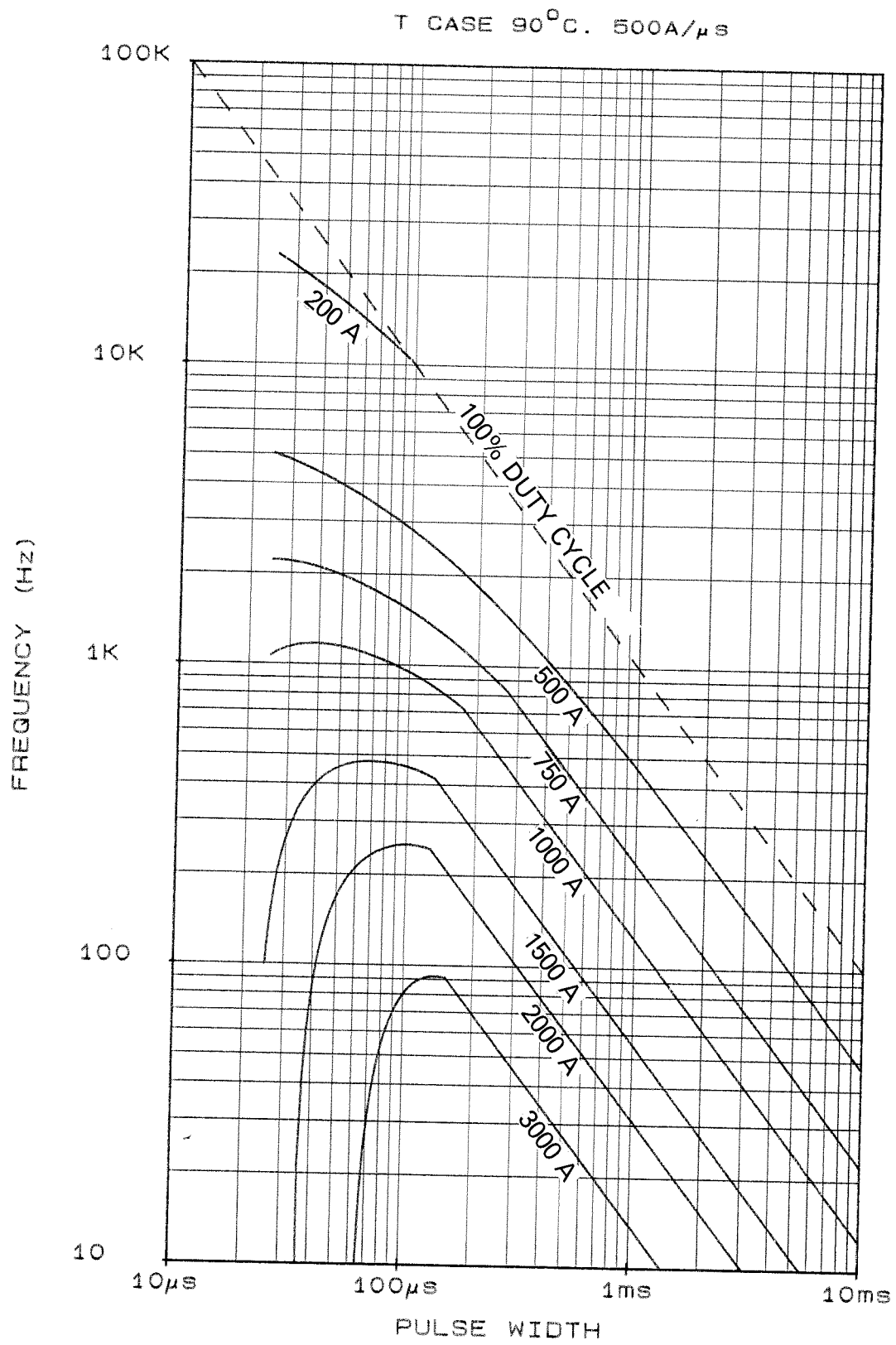
COMMUTATING di/dt AMPS/μs

* NOTE: ENERGY PER PULSE SHOULD BE ADJUSTED PRO RATA WITH APPLIED PEAK RECOVERY VOLTAGE

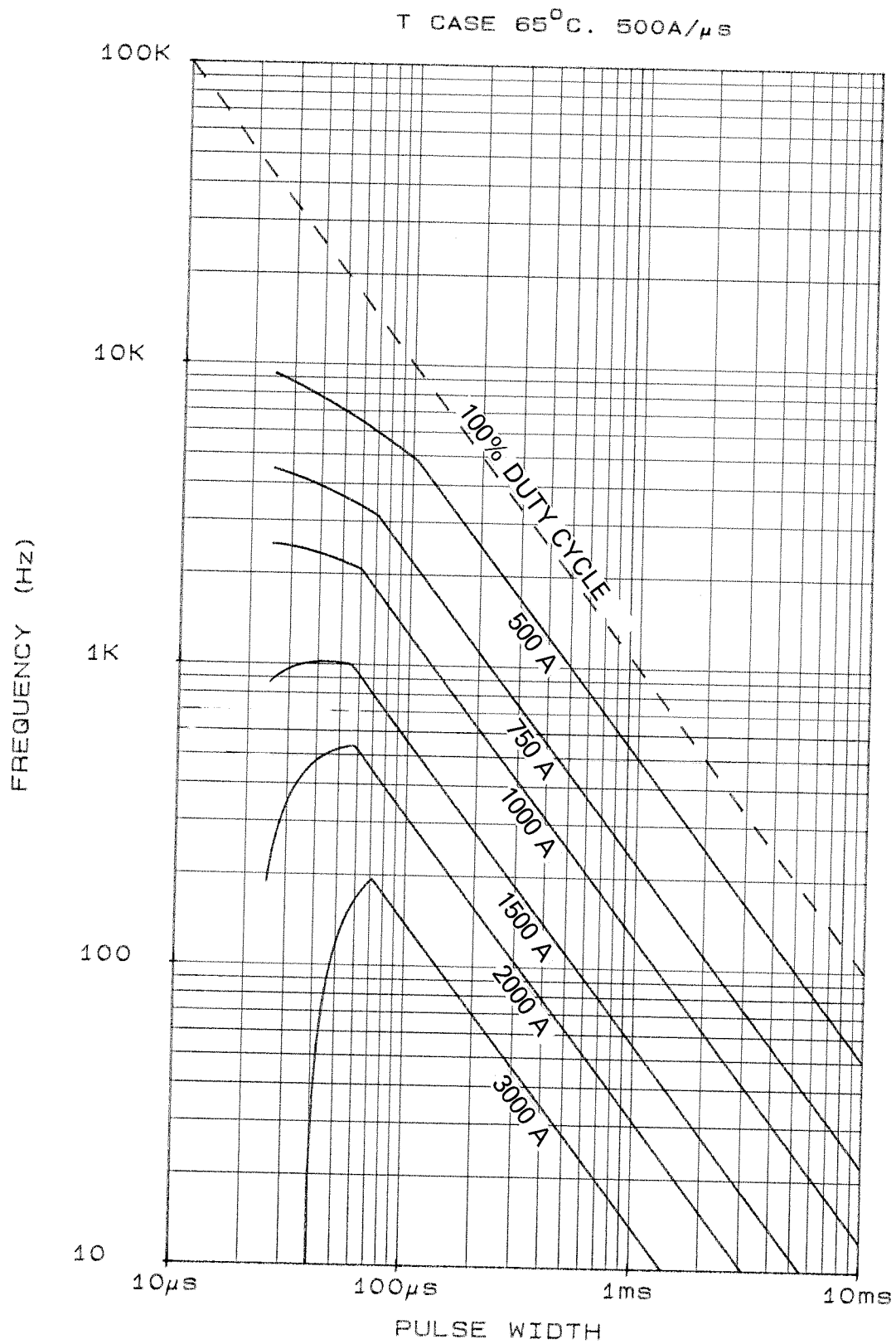




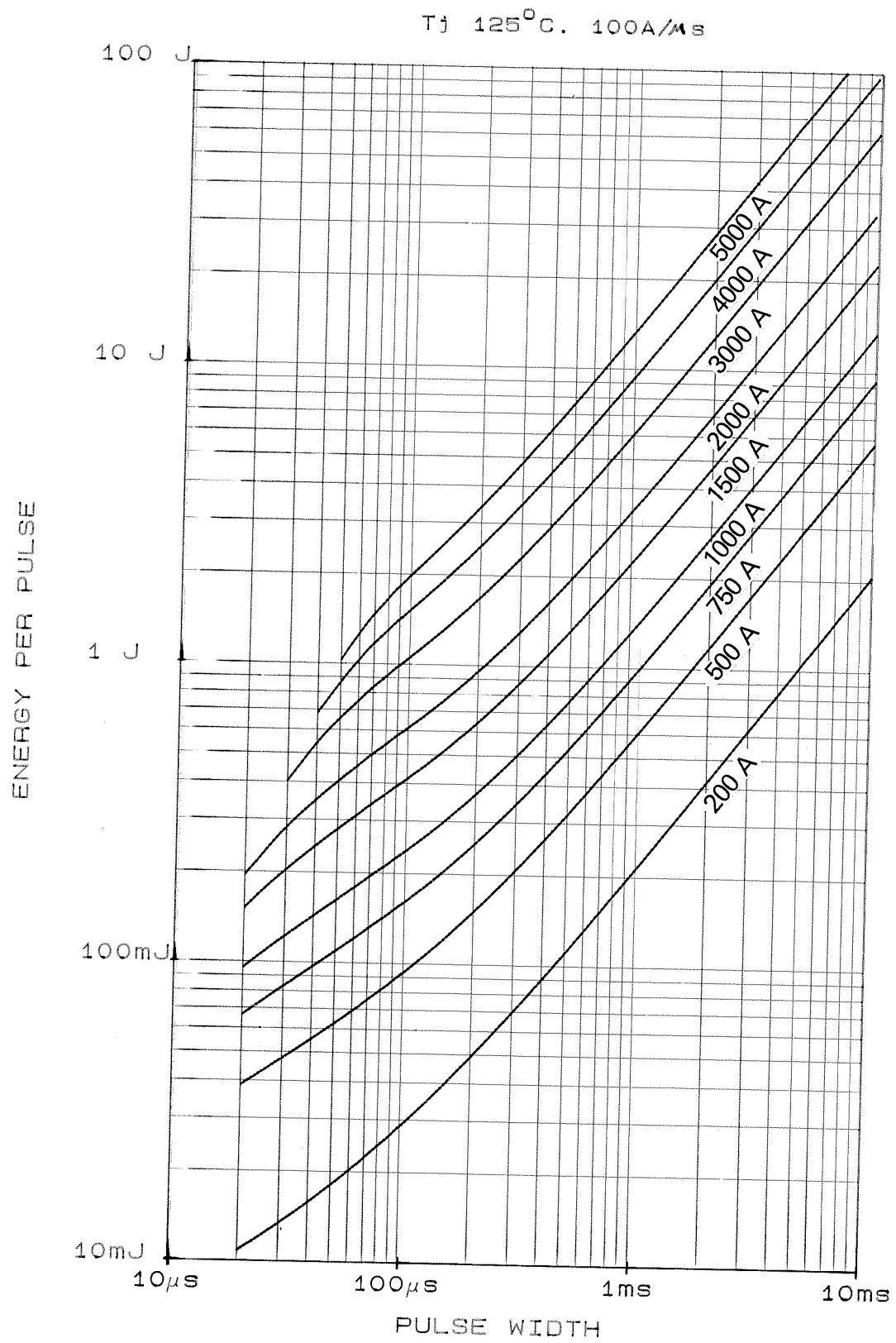
270-4

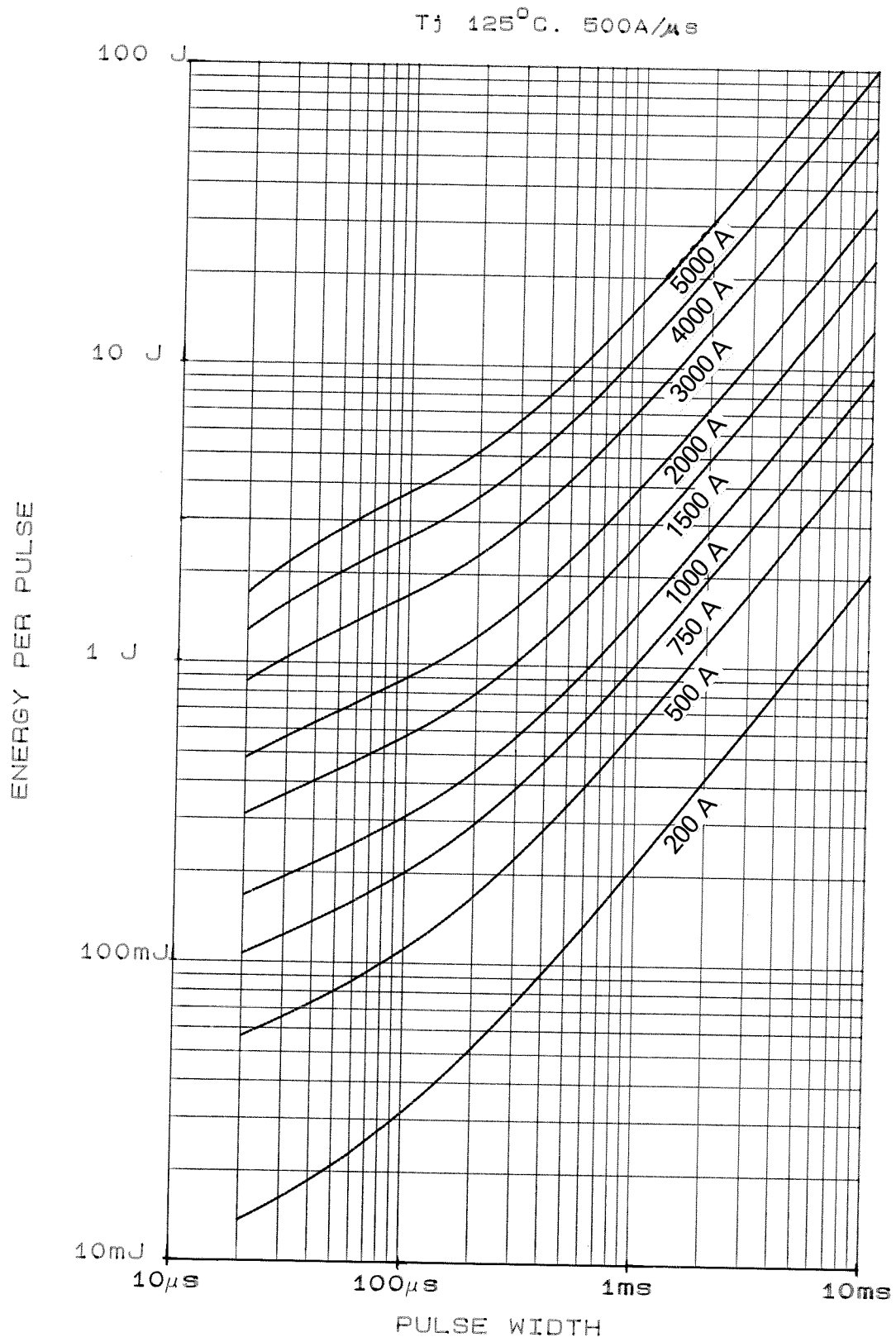


P270P Fig 3

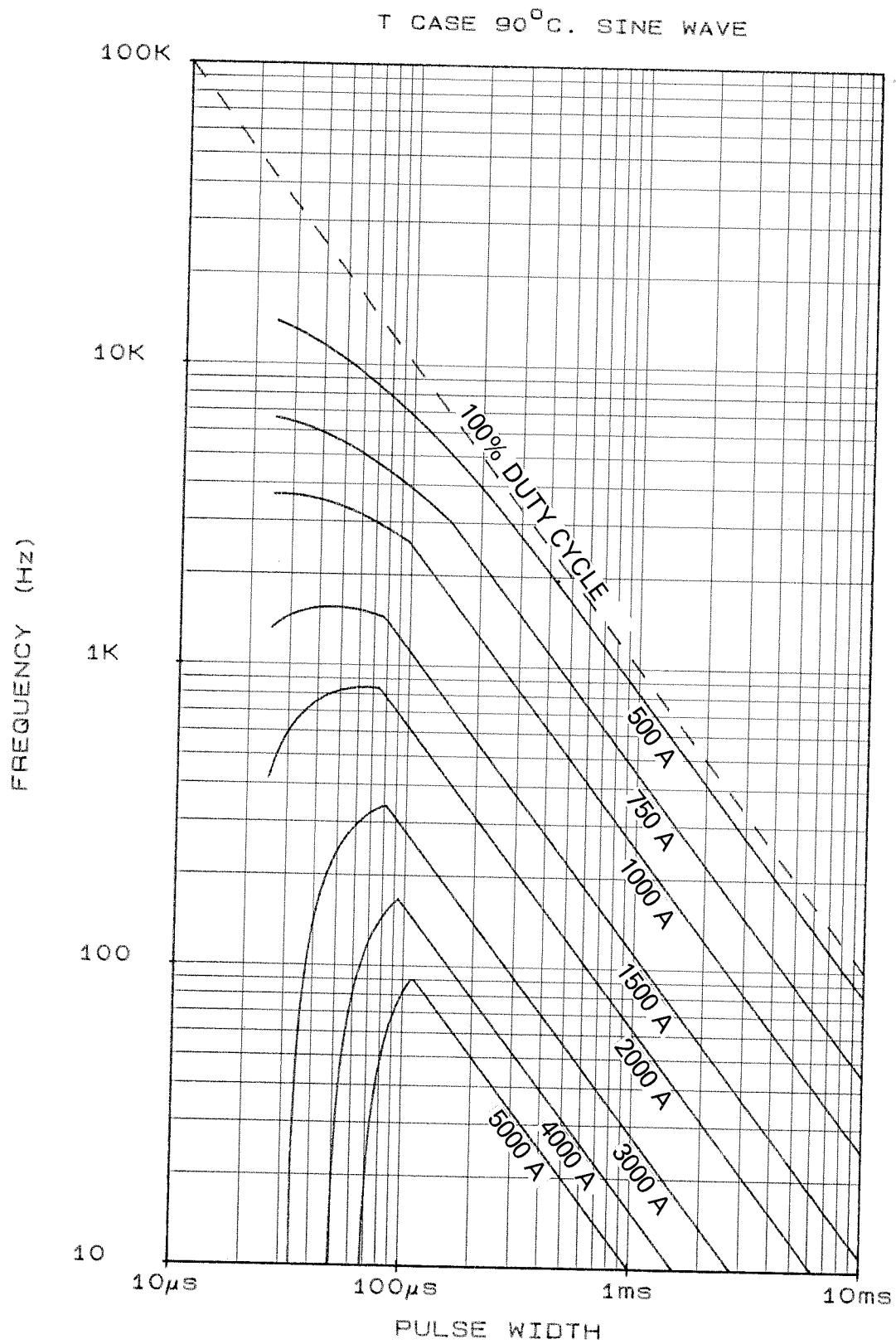


270-3

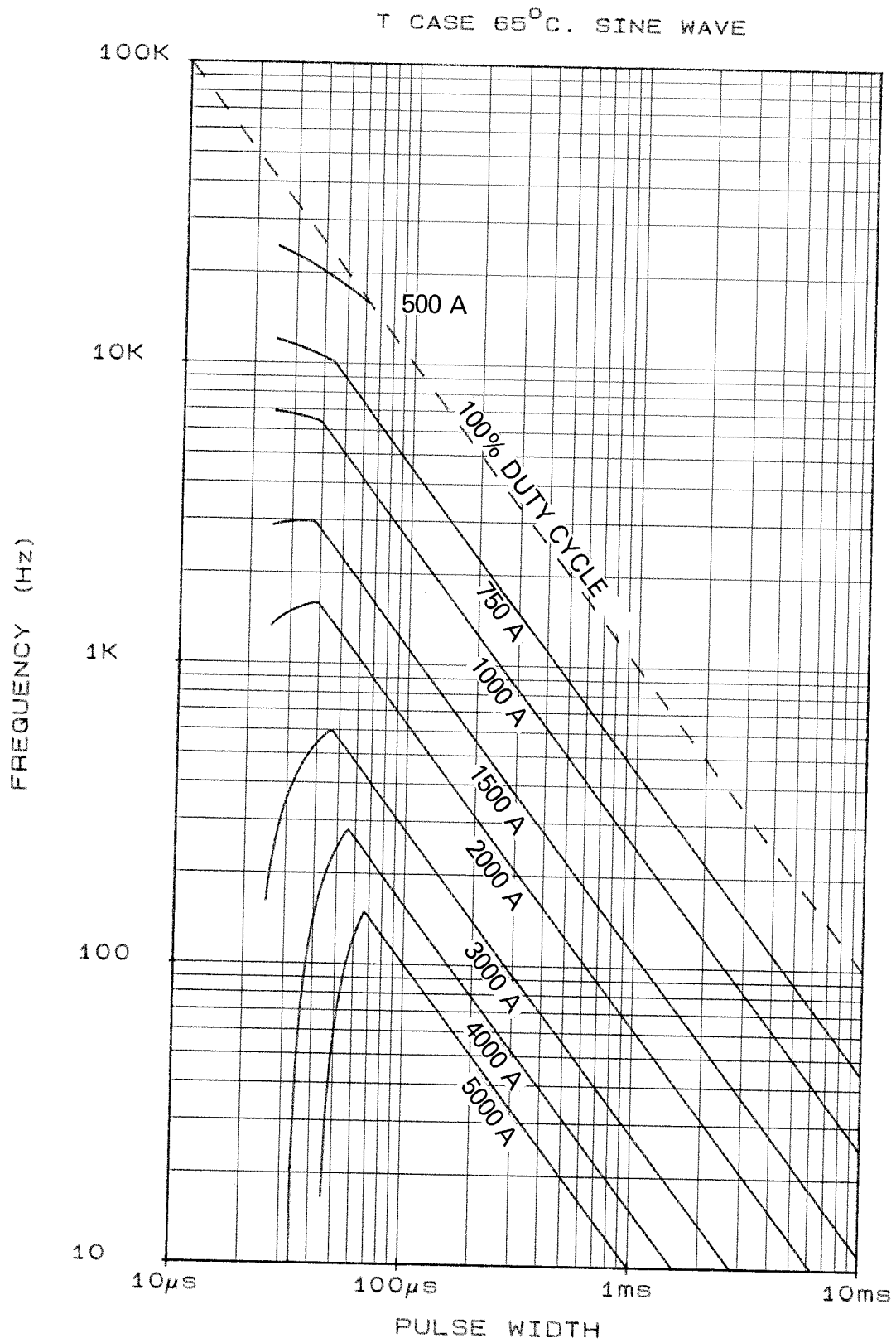




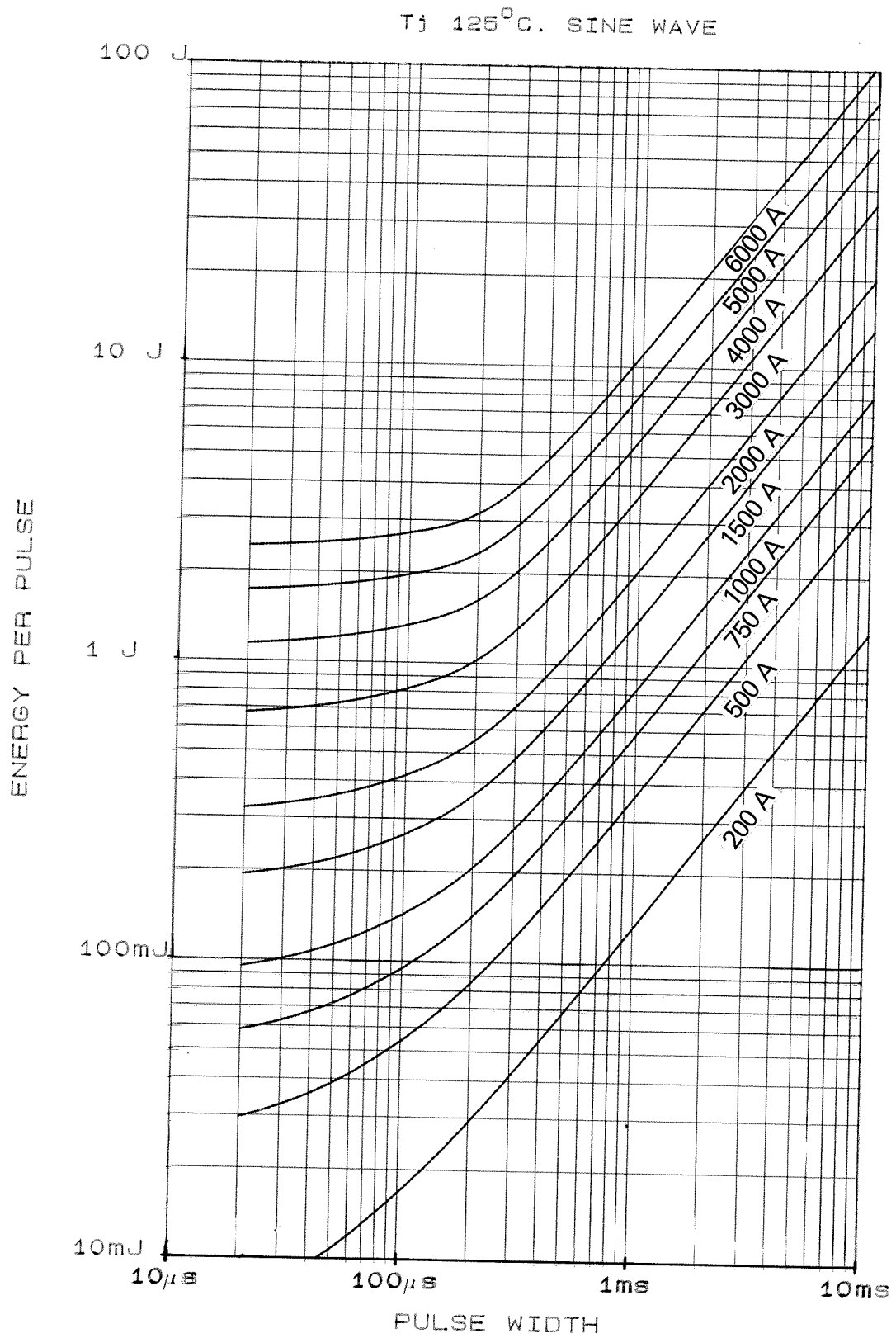
P270P Fig 8



270-8



P9-510 115 9



270-9

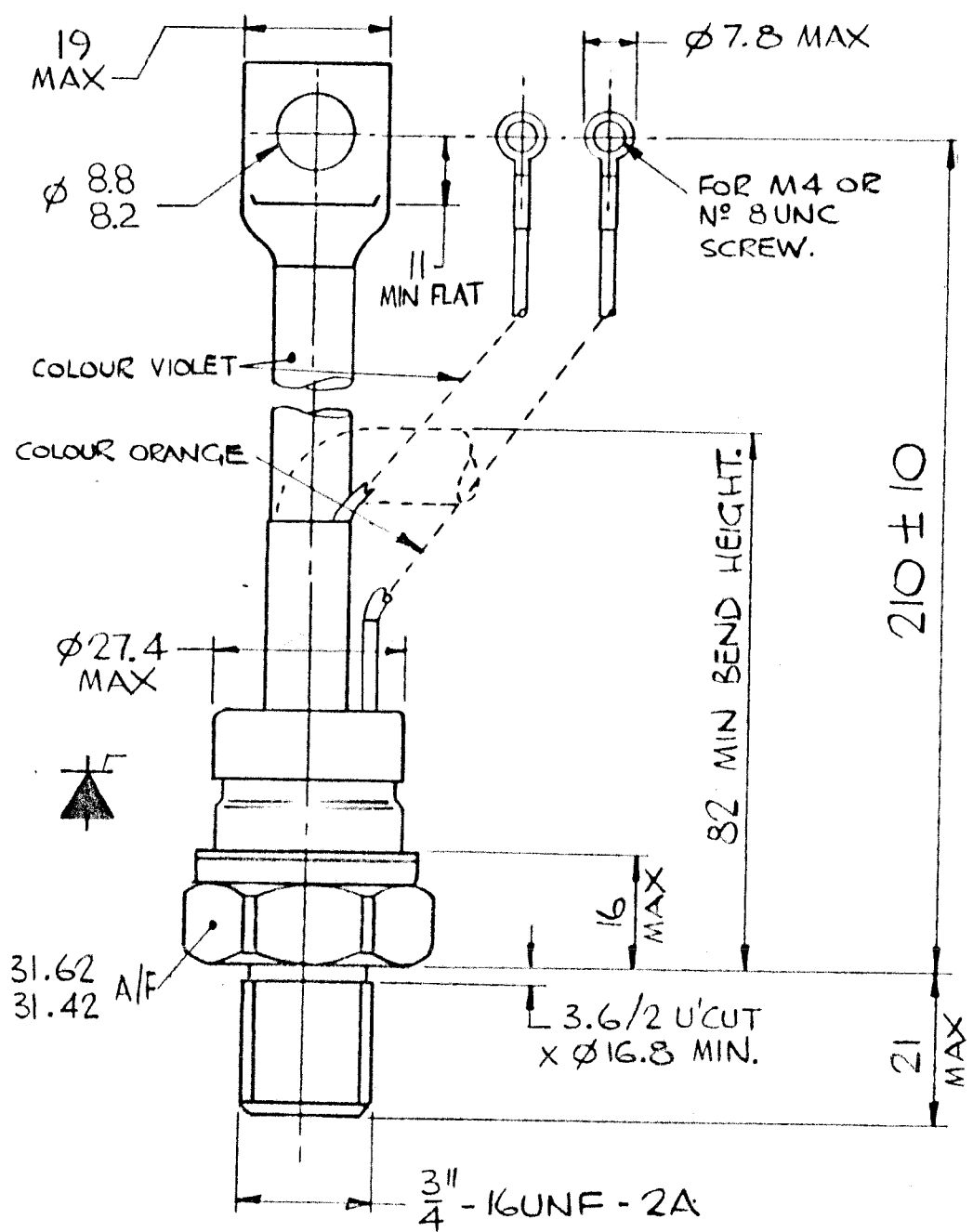
SCALE	1/1
DRN	RS
CHKD	
APPD	
S	A
S	NI

INTERNATIONAL OUTLINE No.
 WEIGHT. 280 GRAMS APPX. - 24 -
 FINISH. BRIGHT NICKEL PLATE.
 DEVICE MARKING INCLUDES MONOGRAM, TYPE No., SPEC.
 No. AND POLARITY SYMBOL.
 DEVICE MOUNTING: MOUNTING TORQUE
 27-24.5 Nm (2.77-2.5 kgf-m).
 THREAD MUST NOT BE LUBRICATED.

	TYPE NUMBER
N170P	P200P
N195P	P202P
N275P	P204P
	P205P
	P214P
	P215P
	P270P

NOTES.

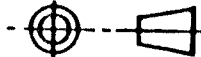
G.A. DRG. No. 103A162



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 SEMICONDUCTORS

THIRD ANGLE PROJECTION


DIMNS. IN MILLIMETRES

DRG. No. 101A225

ISS	REVISIONS
1	19.9.78
2	17.11.78 M670 TYPE N° ADDED
3	8.8/8.2 HOLE WAS 10.7/10.2 H67
4	17.12.79 M817 19 WAS 21.4 H67
5	27.11.84 M1218 FIN WAS ET. H67